

Title (en)

ION IMPLANTATION AND ANNEALING FOR HIGH EFFICIENCY BACK-CONTACT BACK-JUNCTION SOLAR CELLS

Title (de)

IONENIMPLANTATION UND -GLÜHUNG FÜR HOCHEFFIZIENTE SOLARZELLEN MIT RÜCKSEITENKONTAKT UND -BINDUNG

Title (fr)

IMPLANTATION D'ION ET RECUIT POUR DES CELLULES SOLAIRES À RENDEMENT ÉLEVÉ À JONCTION ARRIÈRE ET CONTACT ARRIÈRE

Publication

EP 2715797 A2 20140409 (EN)

Application

EP 12793962 A 20120529

Priority

- US 201161490859 P 20110527
- US 2012039901 W 20120529

Abstract (en)

[origin: WO2012166749A2] A back contact back junction thin-film solar cell is formed on a thin-film semiconductor solar cell. Preferably the thin film semiconductor material comprises crystalline silicon. Emitter regions, selective emitter regions, and a back surface field are formed through ion implantation and annealing processes.

IPC 8 full level

H01L 31/18 (2006.01)

CPC (source: EP KR)

H01L 21/26513 (2013.01 - EP); **H01L 31/02363** (2013.01 - EP); **H01L 31/035281** (2013.01 - EP); **H01L 31/04** (2013.01 - KR); **H01L 31/0682** (2013.01 - EP); **H01L 31/18** (2013.01 - KR); **H01L 31/1804** (2013.01 - EP); **H01L 31/1864** (2013.01 - EP); **H01L 21/26586** (2013.01 - EP); **H01L 21/268** (2013.01 - EP); **H01L 21/324** (2013.01 - EP); **Y02E 10/547** (2013.01 - EP); **Y02P 70/50** (2015.11 - EP)

Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

DOCDB simple family (publication)

WO 2012166749 A2 20121206; WO 2012166749 A3 20130328; EP 2715797 A2 20140409; EP 2715797 A4 20150527; KR 101396027 B1 20140519; KR 20140041602 A 20140404

DOCDB simple family (application)

US 2012039901 W 20120529; EP 12793962 A 20120529; KR 20137034723 A 20120529